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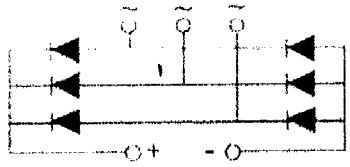
DF100AA120

Three Phases Rectifying Bridge Module

FEATURES

- The chips are electrically insulated from bosom plate ,2500V AC
- High surge current
- Low forward voltage drop
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- AC, DC Motor Drive/AVR/Switching for three phase rectification

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{RRM}	Repetitive Peak Reverse Voltage	T_p=10ms	1200	V
I_O	Output Current (D.C)	Tc=100℃	100	A
I_{FSM}	Surge Forward Current	Half-sine wave,10ms, V_R=0.6V_{RRM}	1800	A
I^2t	I^2t for fusing		16500	A^2S
V_{iso}	Maximum Power Dissipation	50Hz,R.M.S,t=1ms,I_{iso}=1mA(max)	2500	V
T_J	Junction Temperature		-40~125	℃
T_{stg}	Storage Temperature Range		-40~125	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\,j\text{-}c}$	Thermal Resistance, Junction to Case	0.1	℃/W

Quality Semi-Conductors

DF100AA120

Three Phases Rectifying Bridge Module

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Forward Voltage drop	I_F=230A	1.35	V
I_{RRM}	Repetitive Peak Reverse Current	$V_R=V_{RRM}$, T_J=150℃	5	mA

OUTLINE DRAWING

Dimensions in mm (1mm = 0.0394")